



M

E

$T_C = 25$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	65	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_{D@TC=25}$	68	A
	$I_{D@TC=75}$	52	A

Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}			2.2	° C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	62	° C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	° C

I G

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	65			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	1.5		2.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = 0.8 BV_{DSS},$ $V_{GS} = 0V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			100	nA
Static Drain-source On Resistance	!	$V_{GS} = 10V, I_D = 10A$				
		$V_{GS} = 4.5V, I_D = 5A$				
Forward Transconductance	g_{FS}	$V_{DS} = 25V, I_D = 10A$				
Source-drain voltage	V_{SD}	$I_S = 10A$				

I G

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Gate Resistance	R_g	$f = 1MHz$		2.1		
Input capacitance	C_{iss}	$f = 1MHz$ V_{DS}				

Note:

;

Fig.1 Gate-Charge Characteristics

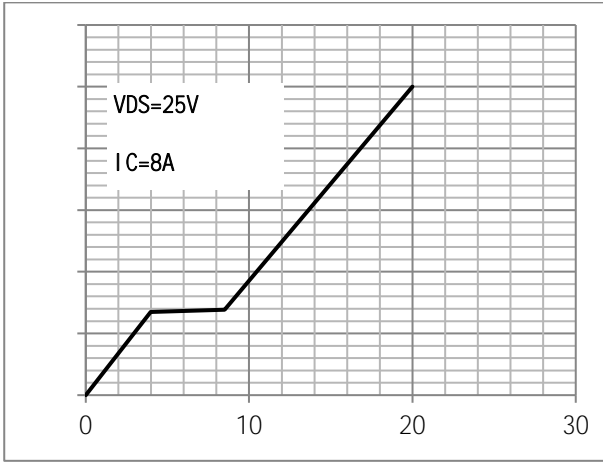


Fig.2 Capacitance Characteristics

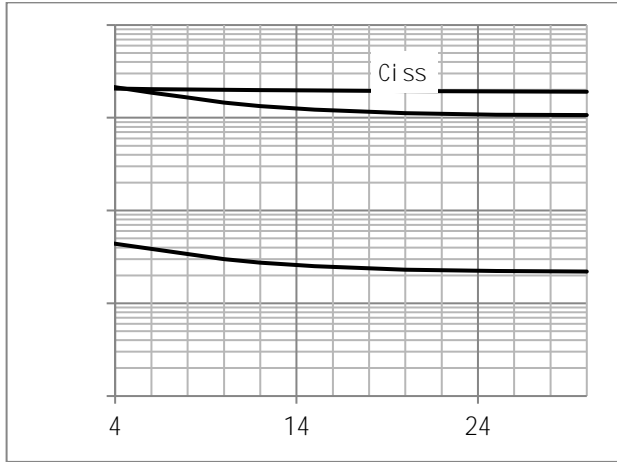


Fig.3 Power Dissipation

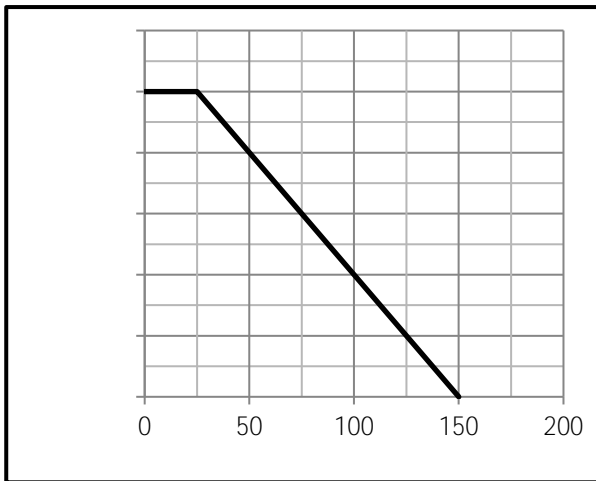


Fig.4 Typical output Characteristics

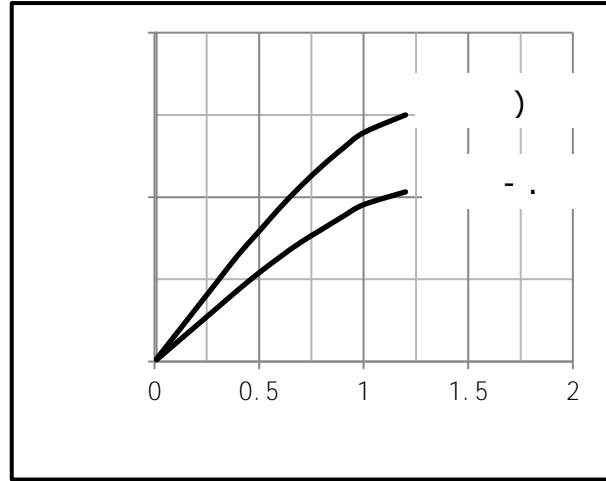


Fig.5 Threshold Voltage V.S Junction Temperature

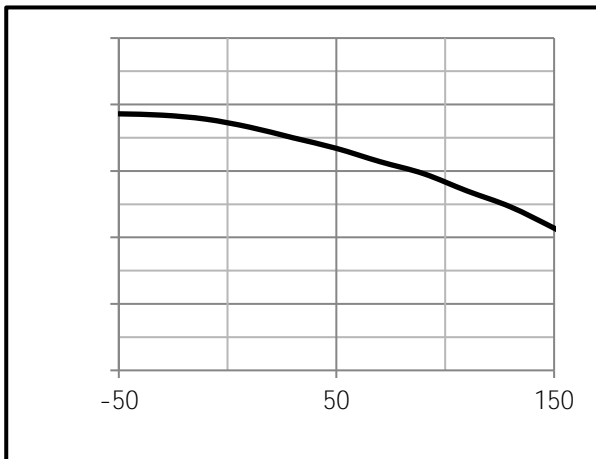
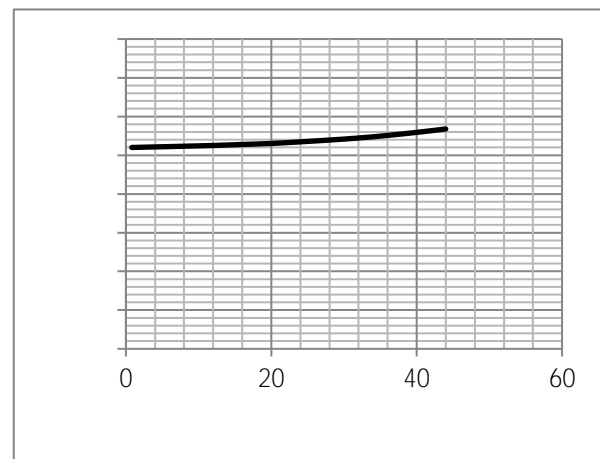
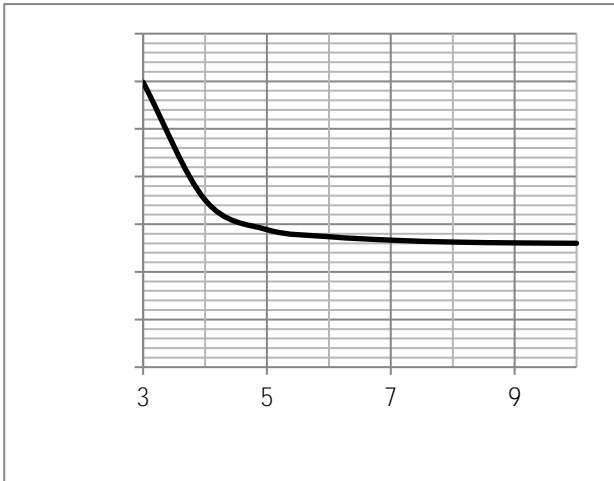


Fig.6 Resistance V.S Drain Current



0



1

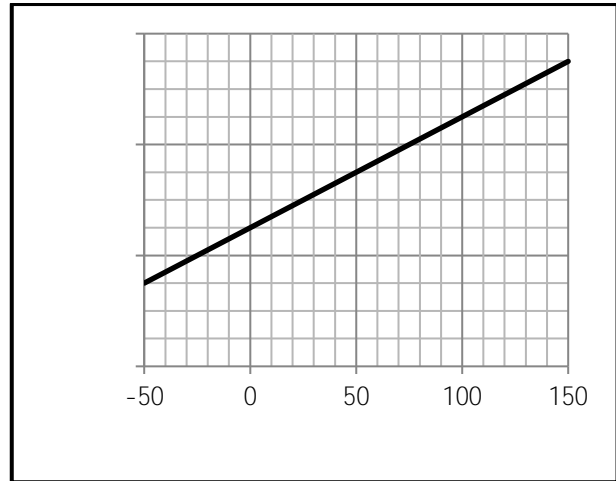


Fig.9 SOA Maximum Safe Operating Area

Fig.10 ID-Junction Temperature

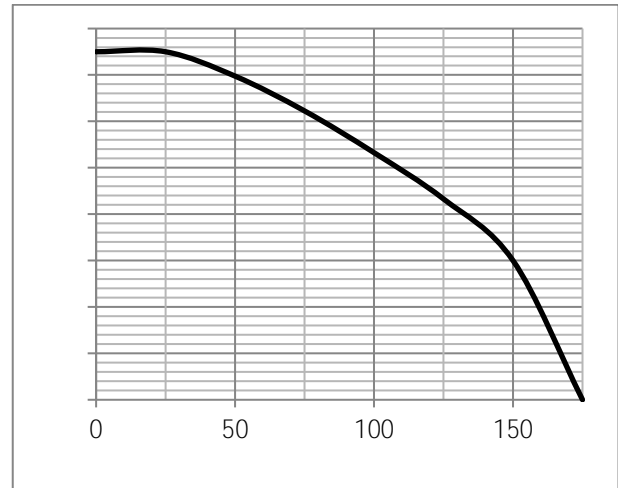
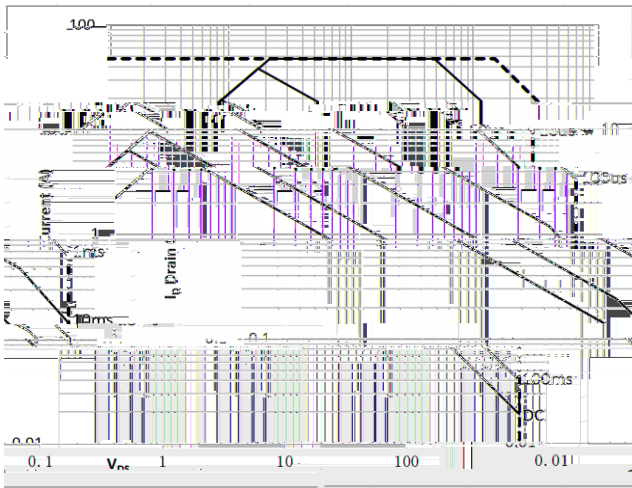


Fig.11 Switching Time Measurement Circuit

Fig.12 Gate Charge Waveform

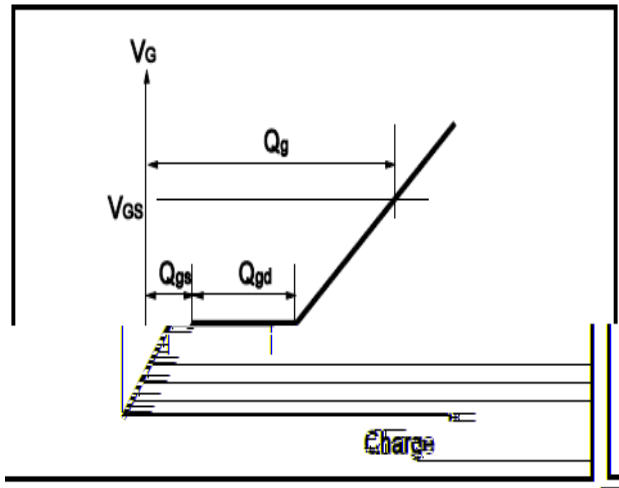
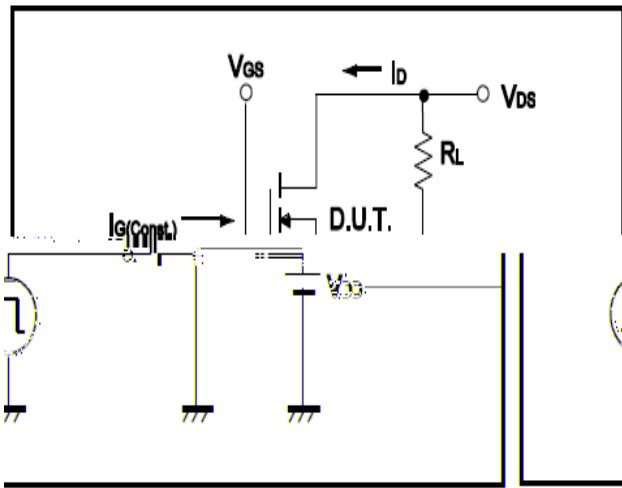


Fig.13 Switching Time Measurement Circuit

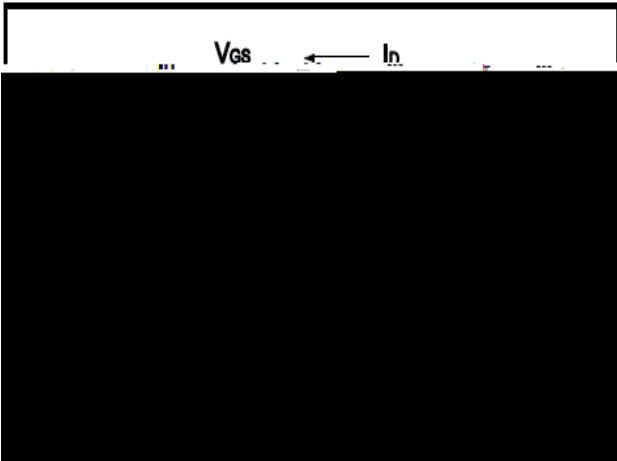


Fig.14 Gate Charge Waveform

